
# PSMN2R9-25YLC

## N-channel 25 V 3.15 mΩ logic level MOSFET in LFPAK using NextPower technology

**Rev. 1 — 2 May 2011** **Product data sheet**

## 1. Product profile

### 1.1 General description

Logic level enhancement mode  N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

### 1.4 Quick reference data

**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | 25 °C ≤ $T_j$ ≤ 175 °C | | - | - | 25 | V |
| $I_D$ | drain current | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 1 | [1] | - | - | 100 | A |
| $P_{tot}$ | total power dissipation | $T_{mb}$ = 25 °C; see Figure 2 | | - | - | 92 | W |
| $T_j$ | junction temperature | | | -55 | - | 175 | °C |

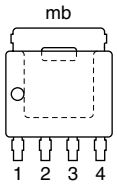
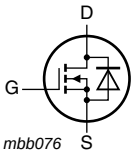
**Table 1. Quick reference data** *...continued*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; see Figure 12 | - | 3.45 | 4.1 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see Figure 12 | - | 2.65 | 3.15 | mΩ |
| **Dynamic characteristics** | | | | | | |
| $Q_{GD}$ | gate-drain charge | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 12 V; see Figure 14; see Figure 15 | - | 4.4 | - | nC |
| $Q_{G(tot)}$ | total gate charge | | - | 16 | - | nC |

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | S | source |   SOT669 (LFPAK; Power-SO8) |   |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

## 3. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PSMN2R9-25YLC | LFPAK; Power-SO8 | plastic single-ended surface-mounted package; 4 leads | SOT669 |

## 4. Marking

**Table 4. Marking codes**

| Type number | Marking code[1] |
|---|---|
| PSMN2R9-25YLC | 2C925L |

[1] % = placeholder for manufacturing site code.

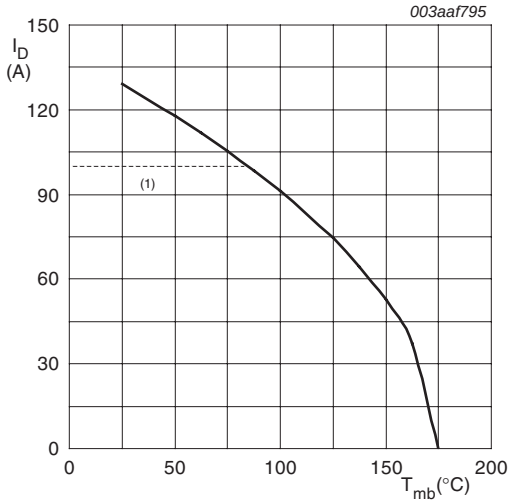
## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

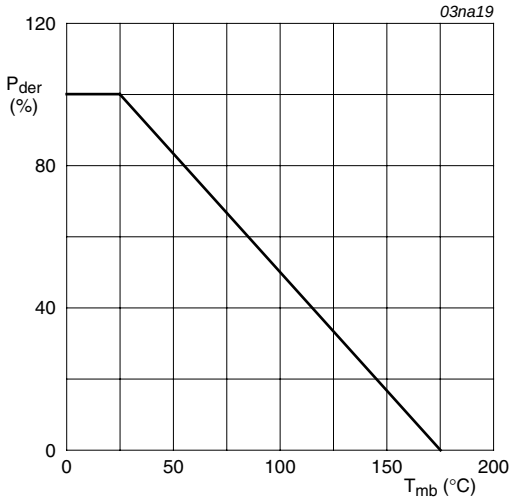
| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | 25 °C ≤ $T_j$ ≤ 175 °C | | - | 25 | V |
| $V_{DGR}$ | drain-gate voltage | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ | | - | 25 | V |
| $V_{GS}$ | gate-source voltage | | | -20 | 20 | V |
| $I_D$ | drain current | $V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see Figure 1 | [1] | - | 100 | A |
| | | $V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see Figure 1 | | - | 91 | A |
| $I_{DM}$ | peak drain current | pulsed; $t_p$ ≤ 10 µs; $T_{mb}$ = 25 °C; see Figure 4 | | - | 517 | A |
| $P_{tot}$ | total power dissipation | $T_{mb}$ = 25 °C; see Figure 2 | | - | 92 | W |
| $T_{stg}$ | storage temperature | | | -55 | 175 | °C |
| $T_j$ | junction temperature | | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | | - | 260 | °C |
| $V_{ESD}$ | electrostatic discharge voltage | MM (JEDEC JESD22-A115) | | 380 | - | V |
| **Source-drain diode** | | | | | | |
| $I_S$ | source current | $T_{mb}$ = 25 °C | | - | 83 | A |
| $I_{SM}$ | peak source current | pulsed; $t_p$ ≤ 10 µs; $T_{mb}$ = 25 °C | | - | 517 | A |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 25 V; unclamped; $R_{GS}$ = 50 Ω; see Figure 3 | | - | 47 | mJ |

[1] Continuous current is limited by package.



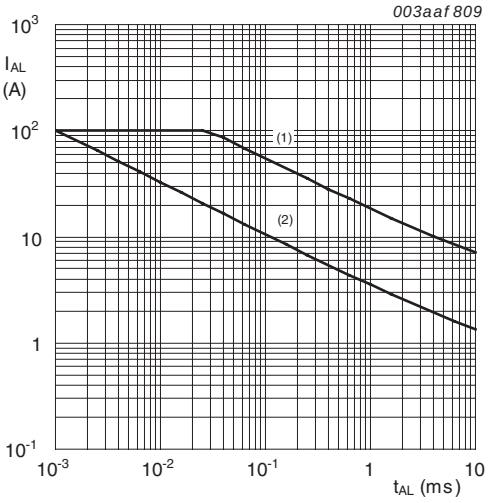

$V_{GS} \geq 10V$; (1) *Capped at 100A due to package*

**Fig 1. Continuous drain current as a function of mounting base temperature**




$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**




(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

**Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time**

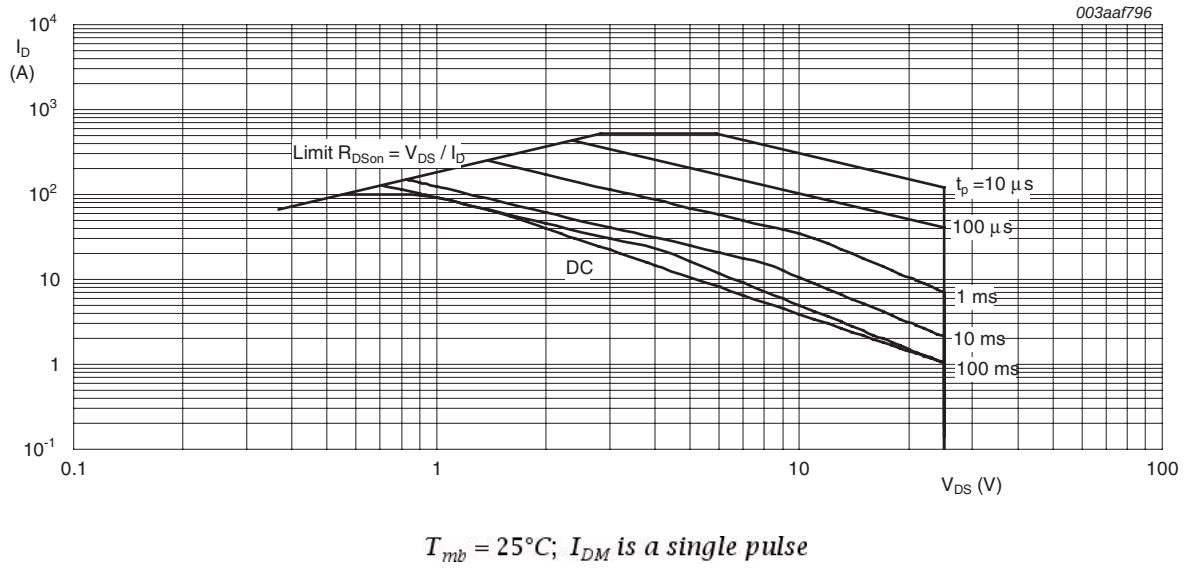



**Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | 1.46 | 1.64 | K/W |

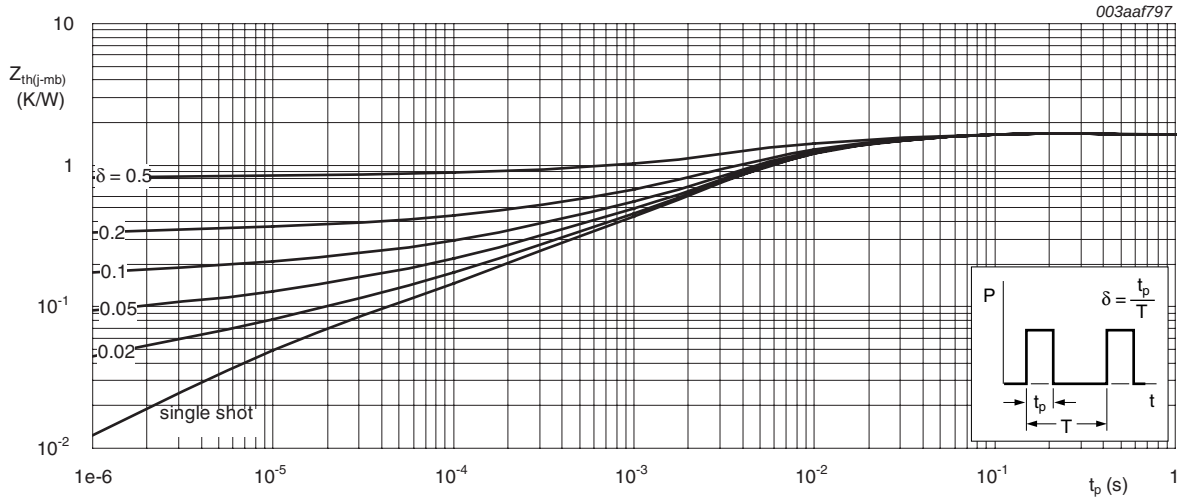



**Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration**

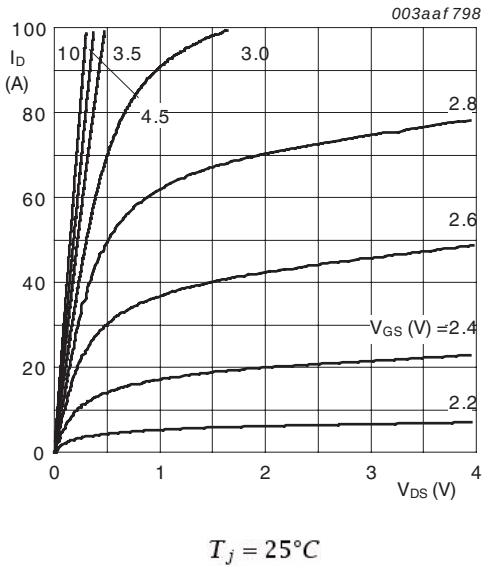
# 7. Characteristics

**Table 7. Characteristics**

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C | 25 | - | - | V |
| | | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C | 22.5 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 25 °C; see Figure 10; see Figure 11 | 1.05 | 1.54 | 1.95 | V |
| | | $I_D$ = 10 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 150 °C | 0.5 | - | - | V |
| | | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = -55 °C | - | - | 2.25 | V |
| $I_{DSS}$ | drain leakage current | $V_{DS}$ = 25 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C | - | - | 1 | µA |
| | | $V_{DS}$ = 25 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C | - | - | 100 | µA |
| $I_{GSS}$ | gate leakage current | $V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | - | - | 100 | nA |
| | | $V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | - | - | 100 | nA |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; see Figure 12 | - | 3.45 | 4.1 | mΩ |
| | | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 150 °C; see Figure 12; see Figure 13 | - | - | 6.6 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see Figure 12 | - | 2.65 | 3.15 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C; see Figure 12; see Figure 13 | - | - | 5.05 | mΩ |
| $R_G$ | gate resistance | f = 1 MHz | - | 2 | 4 | Ω |
| **Dynamic characteristics** | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see Figure 14; see Figure 15 | - | 33 | - | nC |
| | | $I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 4.5 V; see Figure 14; see Figure 15 | - | 16 | - | nC |
| | | $I_D$ = 0 A; $V_{DS}$ = 0 V; $V_{GS}$ = 10 V | - | 29 | - | nC |
| $Q_{GS}$ | gate-source charge | $I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 4.5 V; see Figure 14; see Figure 15 | - | 5 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | - | 3.4 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | - | 1.6 | - | nC |
| $Q_{GD}$ | gate-drain charge | | - | 4.4 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D$ = 25 A; $V_{DS}$ = 12 V; see Figure 14; see Figure 15 | - | 2.55 | - | V |
| $C_{iss}$ | input capacitance | $V_{DS}$ = 12 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; see Figure 16 | - | 2083 | - | pF |
| $C_{oss}$ | output capacitance | | - | 501 | - | pF |
| $C_{rss}$ | reverse transfer capacitance | | - | 160 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS}$ = 12 V; $R_L$ = 0.5 Ω; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 4.7 Ω | - | 19.5 | - | ns |
| $t_r$ | rise time | | - | 19 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 32 | - | ns |
| $t_f$ | fall time | | - | 13 | - | ns |

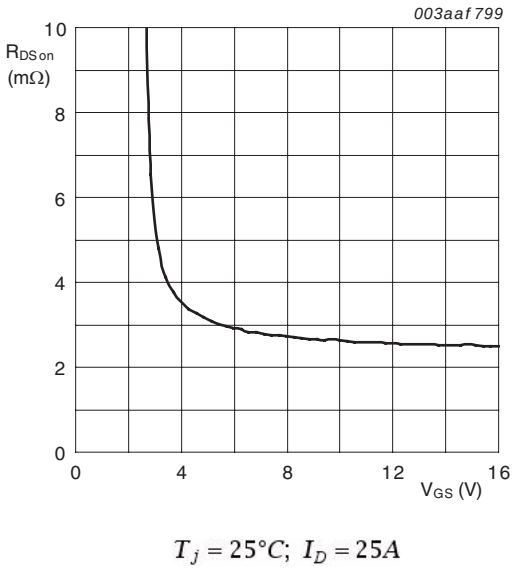
**Table 7. Characteristics** *...continued*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $Q_{oss}$ | output charge | $V_{GS}$ = 0 V; $V_{DS}$ = 12 V; f = 1 MHz; $T_j$ = 25 °C | - | 18.5 | - | nC |
| **Source-drain diode** | | | | | | |
| $V_{SD}$ | source-drain voltage | $I_S$ = 25 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see Figure 17 | - | 0.8 | 1.1 | V |
| $t_{rr}$ | reverse recovery time | $I_S$ = 25 A; $dI_S/dt$ = -100 A/µs; $V_{GS}$ = 0 V; $V_{DS}$ = 12 V | - | 32 | - | ns |
| $Q_r$ | recovered charge | | - | 23 | - | nC |
| $t_a$ | reverse recovery rise time | $V_{GS}$ = 0 V; $I_S$ = 25 A; $dI_S/dt$ = -100 A/µs; $V_{DS}$ = 12 V; see Figure 18 | - | 18 | - | ns |
| $t_b$ | reverse recovery fall time | | - | 14 | - | ns |



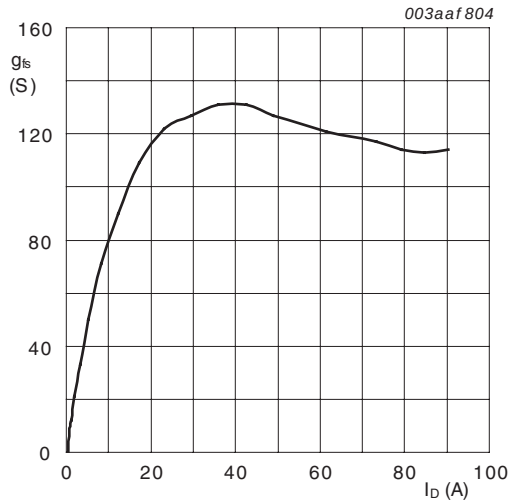

$T_j = 25°C$

**Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



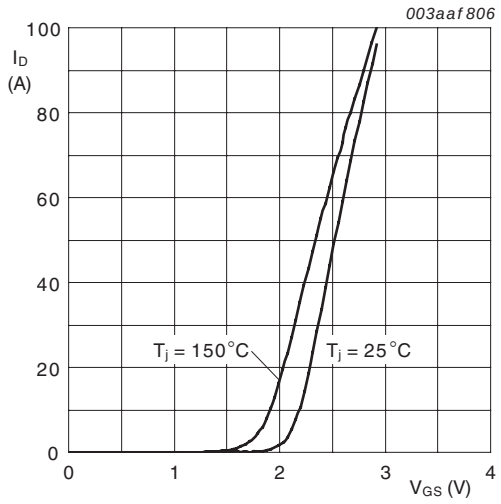

$T_j = 25°C;\ I_D = 25A$

**Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**



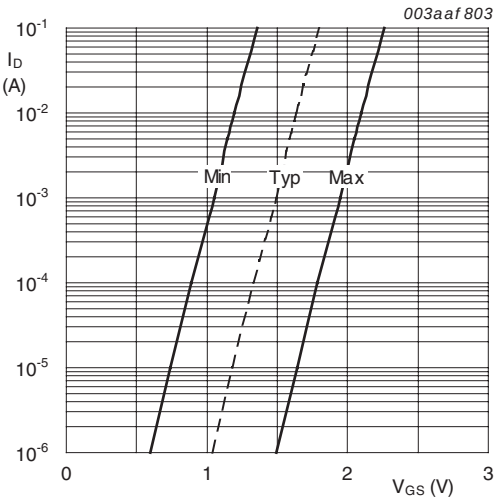

$T_j = 25°C;\ V_{DS} = 10V$

**Fig 8. Forward transconductance as a function of drain current; typical values**



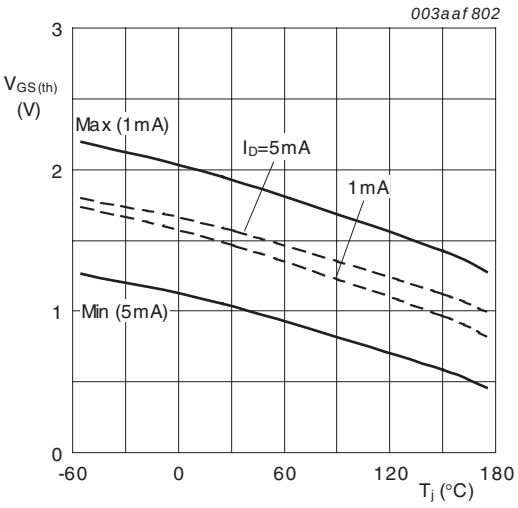

$V_{DS} = 10V$

**Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



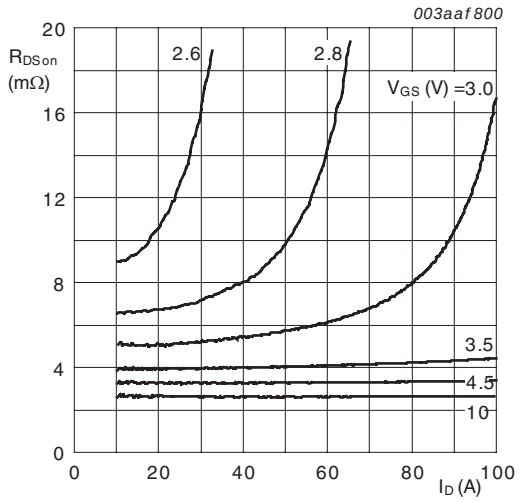

$T_j = 25°C;\ V_{DS} = 5V$

**Fig 10. Sub-threshold drain current as a function of gate-source voltage**



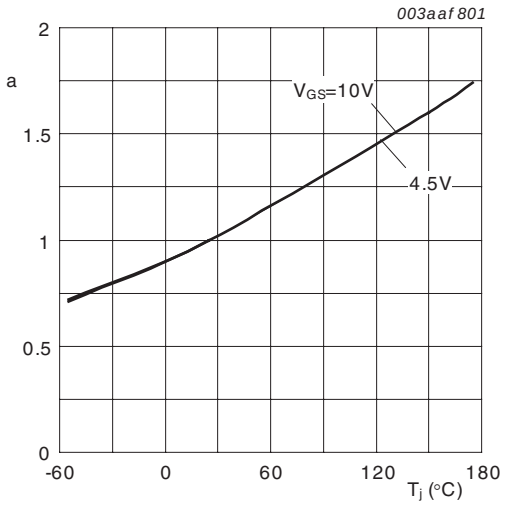

$V_{DS} = V_{GS}$

**Fig 11. Gate-source threshold voltage as a function of junction temperature**




$T_j = 25°C$

**Fig 12. Drain-source on-state resistance as a function of drain current; typical values**




$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

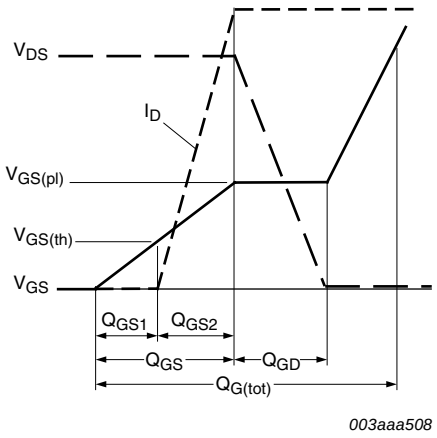
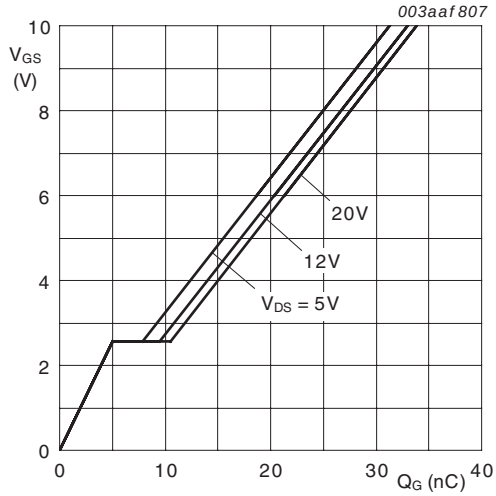
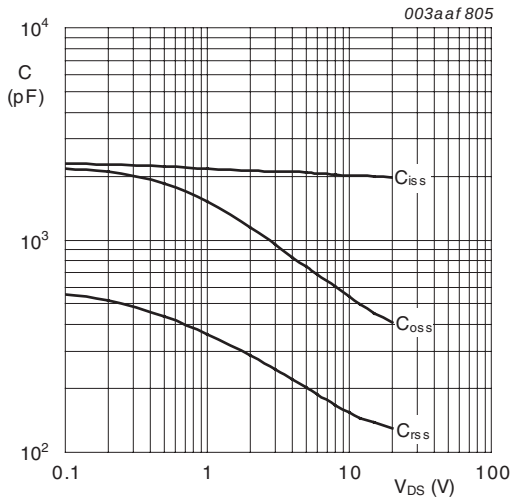



**Fig 14. Gate charge waveform definitions**



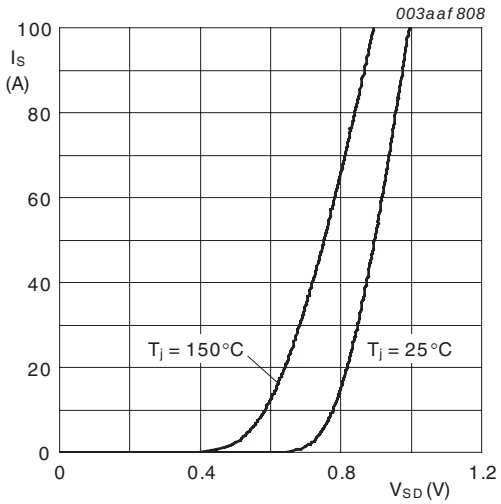

$T_j = 25°C;\ I_D = 25A$

**Fig 15. Gate-source voltage as a function of gate charge; typical values**




$V_{GS} = 0V;\ f = 1MHz$

**Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**




$V_{GS} = 0V$

**Fig 17. Source current as a function of source-drain voltage; typical values**

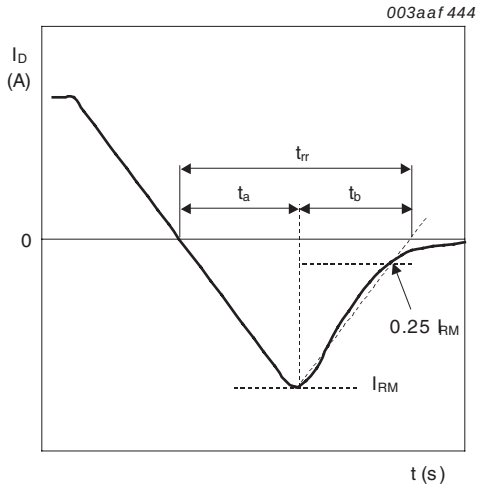
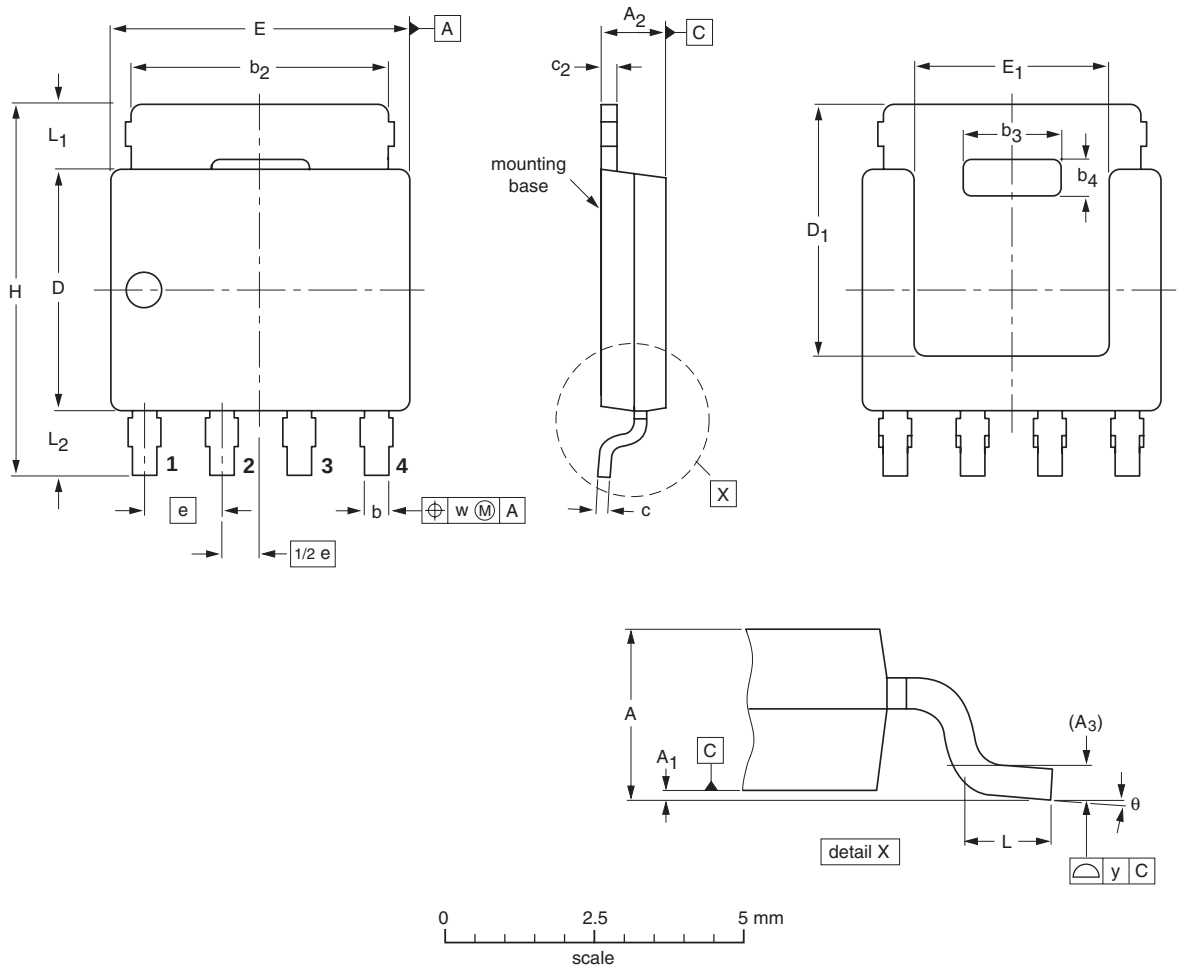



**Fig 18. Reverse recovery timing definition**

# 8. Package outline

**Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads** **SOT669**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A | $A_1$ | $A_2$ | $A_3$ | b | $b_2$ | $b_3$ | $b_4$ | c | $c_2$ | $D^{(1)}$ | $D_1^{(1)}$ max | $E^{(1)}$ | $E_1^{(1)}$ | e | H | L | $L_1$ | $L_2$ | w | y | θ |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 1.20<br>1.01 | 0.15<br>0.00 | 1.10<br>0.95 | 0.25 | 0.50<br>0.35 | 4.41<br>3.62 | 2.2<br>2.0 | 0.9<br>0.7 | 0.25<br>0.19 | 0.30<br>0.24 | 4.10<br>3.80 | 4.20 | 5.0<br>4.8 | 3.3<br>3.1 | 1.27 | 6.2<br>5.8 | 0.85<br>0.40 | 1.3<br>0.8 | 1.3<br>0.8 | 0.25 | 0.1 | 8°<br>0° |

**Note**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT669 | | MO-235 | | | | ~~06-03-16~~<br>11-03-25 |

**Fig 19. Package outline SOT669 (LFPAK; Power-SO8)**

# 9. Revision history

**Table 8. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| PSMN2R9-25YLC v.1 | 20110502 | Product data sheet | - | - |

# 10. Legal information

## 10.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 11. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

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